WHAT IS CLAIMED IS:

1. A liquid crystal display device, comprising:

first and second substrates facing each other;

a gate line and a data line arranged substantially perpendicular to one another on the first substrate and defining a pixel region;

a thin film transistor at crossing of the gate line and the data line;

a passivation layer in a stripe form on the data line and the thin film transistor; and

liquid crystal between the first and second substrates.

2. The device of claim 1, wherein the thin film transistor comprises: a gate electrode;

a semiconductor layer on the gate electrode; and source/drain electrodes on the semiconductor layer.

3. The device of claim 1, further comprising:

a gate insulation layer formed between the gate line and the data line.

4. The device of claim 2, wherein the striped passivation film is formed to partially overlap the drain electrode such that a portion of the drain electrode of the thin film transistor is not covered by the passivation film.

5. The device of claim 2, further comprising:

a pixel electrode connected to the drain electrode.

6. The device of claim 1, further comprising:

a storage electrode on the gate line.

7. The device of claim 1, further comprising:

a storage line substantially parallel to the gate line and on the same layer as the gate line.

8. The device of claim 1, further comprising:

a storage line substantially parallel to the data line and on the same layer as the data line.

9. The device of claim 1, wherein the passivation layer has a constant width.

10. A method for fabricating a liquid crystal display device, comprising:

providing a first substrate;

forming a gate electrode and a gate line on the substrate;

forming a semiconductor layer pattern on the gate electrode;

forming source/drain electrode and a data line substantially perpendicular to the gate line and crossing the gate line to define a pixel region;

forming a striped passivation layer on the data line and on the thin film transistor;

providing a second substrate facing the first substrate; and

providing liquid crystal between the first and second substrate.

11. The method of claim 10, wherein forming a passivation layer comprises:

providing a cliché having a groove;

filling a resist into the groove;

applying the resist filled in the groove of the cliché onto an etching objection layer on the first substrate; and

etching the etching objection layer by using the resist applied on an etching objection layer as a mask..

12. The method of claim 11, wherein applying the resist to the etching object layer comprises:

transferring the resist filled in the groove of the cliché onto the surface of a printing roll; and

applying the resist of the printing roll onto the etching object layer by rotating the printing roll.

13. The method of claim 11, wherein the etching object layer is an insulation layer.

14. The method of claim 13, wherein the insulation layer contains inorganic material such as SiOx or SiNx.

15. The method of claim 13, wherein the insulation layer contains an organic material such as BCB (benzocyclobutene) or acryl.

16. The method of claim 10, further comprising:

forming a pixel electrode contacting the drain electrode in the pixel region.

17. The method of claim 16, wherein a portion of the pixel electrode is formed on the drain electrode not covered by the striped passivation film.

18. The method of claim 10, further comprising:

forming a storage electrode over the gate line when the source/drain electrode is formed.

19. The method of claim 10, further comprising:

forming a storage line substantially parallel with the gate line in the pixel region.

20. The method of claim 19, wherein the storage line is formed at the same time that the gate line is formed.

21. The method of claim 18, wherein the storage line is formed substantially parallel to and adjacent to the data line in the pixel region.

22. The method of claim 21, wherein the storage line is formed at the same time that the data line is formed.

23. The method of claim 10, wherein the passivation layer has a constant width.

24. A method of fabricating a liquid crystal display device, comprising:

providing a first substrate;

forming a gate electrode and a gate line on the substrate;

forming a semiconductor layer pattern on the gate electrode;

forming source/drain electrode and a data line substantially perpendicular to the gate line and crossing the gate line to define a pixel region;

forming a passivation layer on the data line and on the thin film transistor by roll printing an organic material onto the first substrate;

providing a second substrate facing the first substrate; and

providing liquid crystal between the first and second substrate.

25. The method of claim 24, further comprising:

forming a pixel electrode contacting the drain electrode in the pixel region.

26. The method of claim 25, wherein a portion of the pixel electrode is formed on the drain electrode not covered by the striped passivation film.

27. The method of claim 24, further comprising:

forming a storage electrode over the gate line when the source/drain electrode is formed.

28. The method of claim 24, further comprising:

forming a storage line substantially parallel with the gate line in the pixel region.

29. The method of claim 28, wherein the storage line is formed at the same time that the gate line is formed.

30. The method of claim 29, wherein the storage line is formed substantially parallel to and adjacent to the data line in the pixel region.

31. The method of claim 30, wherein the storage line is formed at the same time that the data line is formed.

32. The method of claim 24, wherein the passivation layer has a constant width.

33. The method of claim 24, wherein the organic material contains BCB (benzocyclobutene), polyimide or acryl.